

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

<u>Vishay Semiconductor/Diodes Division</u> <u>VESD12A1C-HD1-GS08</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Datasheet of VESD12A1C-HD1-GS08 - TVS DIODE 12VWM 23VC LLP1006

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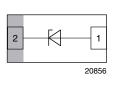
VESD12A1C-HD1

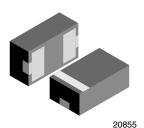
HALOGEN FREE

GREEN

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ESD-Protection Diode in LLP1006-2L





MARKING (exa



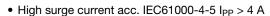
Bar = cathode marking

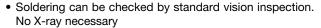
X = date code

Y = type code (see table below)

FEATURES

- Ultra compact LLP1006-2L package
- Low package height < 0.4 mm
- 1-line ESD-protection
- Low leakage current < 0.01 μA
- Low load capacitance C_D = 12.5 pF $(V_R = 6 V; f = 1 MHz)$
- ESD-protection acc. IEC 61000-4-2 ± 30 kV contact discharge ± 30 kV air discharge





- Pin plating NiPdAu (e4) no whisker growth
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

amı	ole only)	
	XY	

ORDERING INFORMATION					
DEVICE NAME ORDERING CODE		TAPED UNITS PER REEL (8 mm TAPE ON 7" REEL)	MINIMUM ORDER QUANTITY		
VESD12A1C-HD1	VESD12A1C-HD1-GS08	8000	8000		

PACKAGE DATA						
DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
VESD12A1C-HD1	LLP1006-2L	G	0.72 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals

ABSOLUTE MAXIMUM RATINGS VESD12A1C-HD1						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Acc. IEC 61000-4-5; t _p = 8/20 μs; single shot	I _{PPM}	4	Α		
Peak pulse power	Acc. IEC 61000-4-5; t _p = 8/20 μs; single shot	P _{PP}	92	W		
ECD improvedity	Contact discharge, acc. IEC61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
ESD immunity		± 30	kV			
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

PATENT(S): www.vishay.com/patents

This Vishay product is protected by one or more United States and International patents.

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VESD12A1C-HD1

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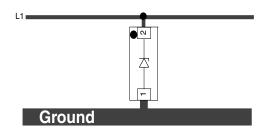
BIAs-MODE (Bidirectional asymmetrical protection mode)

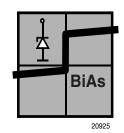
With the VESD12A1C-HD1 one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 2 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified maximum reverse working voltage (V_{RWM}) the protection diode between data line and ground offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the break through voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The clamping voltage (V_C) is defined by the breakthrough voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection device.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction of the protection diode. The low forward voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the VESD12A1C-HD1 clamping behavior is bidirectional and asymmetrical (BiAs).





ELECTRICAL CHARACTERISTICS VESD12A1C-HD1 BiAs mode (between pin 1 and pin 2) (T _{amb} = 25 °C, unless otherwise specified)							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	- 1 line		
Reverse stand-off voltage	Max. reverse working voltage	V_{RWM}	-	-	12	V	
Reverse voltage	at I _R = 0.1 μA	V_R	12	-	-	V	
Reverse current	at V _{RWM} = 12 V	I _R	-	< 0.01	0.1	μA	
Reverse breakdown voltage	at I _R = 1 mA	V_{BR}	13.5	14	16	V	
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	15.8	17	V	
	at I _{PP} = I _{PPM} = 4 A	V _C	-	20	23	V	
Forward clamping voltage	at I _{PP} = 0.2 A	V_{F}		0.9	1.2	V	
	at I _{PP} = 1 A	V_{F}		1.1	1.5	V	
	at I _{PP} = I _{PPM} = 4 A	V_{F}		1.7	2.1	V	
Capacitance	at $V_R = 0 V$; $f = 1 MHz$	C _D	-	30	36	pF	
	at V _R = 6 V; f = 1 MHz	C _D	1	12.5	-	pF	

VESD12A1C-HD1

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TYPICAL CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

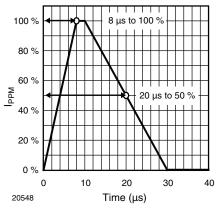


Fig. 1 - 8/20 µs Peak Pulse Current Wave Form (acc. IEC 61000-4-5)

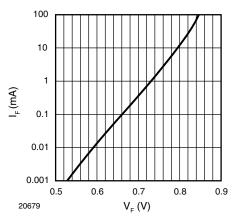


Fig. 4 - Typical Forward Current I_F vs. Forward Voltage V_F

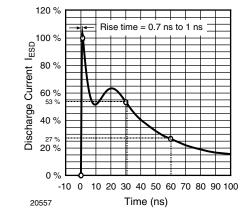


Fig. 2 - ESD Discharge Current Wave Form acc. IEC 61000-4-2 (330 Ω /150 pF)

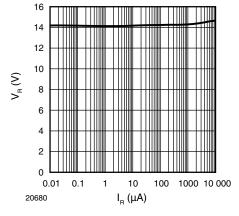


Fig. 5 - Typical Reverse Voltage $V_{\mbox{\scriptsize R}}$ vs. Reverse Current $I_{\mbox{\scriptsize R}}$

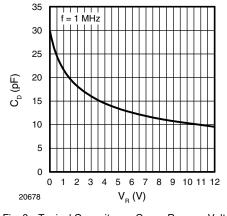


Fig. 3 - Typical Capacitance $C_{\mbox{\scriptsize D}}$ vs. Reverse Voltage $V_{\mbox{\scriptsize R}}$

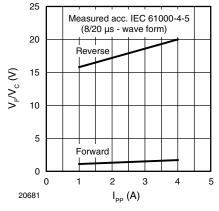


Fig. 6 - Typical Clamping Voltage vs. Peak Pulse Current IPP

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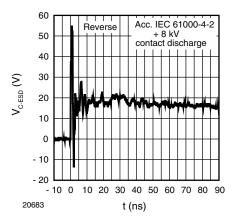


Fig. 7 - Typical Clamping Performance at + 8 kV Contact Discharge (acc. IEC 61000-4-2)

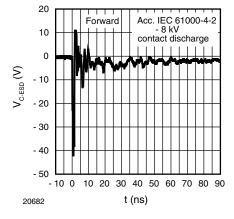


Fig. 8 - Typical Clamping Performance at - 8 kV Contact Discharge (acc. IEC 61000-4-2)

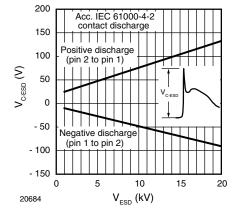


Fig. 9 - Typical Clamping Voltage at ± ESD Contact Discharge Fig. 10 - (acc. IEC 61000-4-2)

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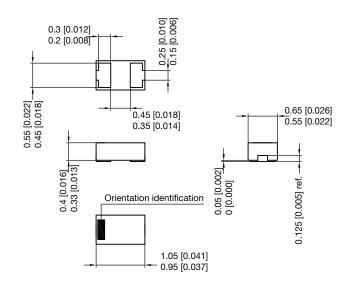
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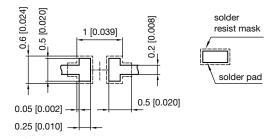
VESD12A1C-HD1

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PACKAGE DIMENSIONS in millimeters (inches): LLP1006-2L



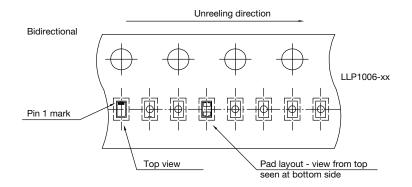
Foot print recommendation:



Pad Design Patented: (@US 9.018.537 B2)

Document no.: S8-V-3906.04-005 (4) Rev. 7 - Date: 11.May 2016

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